

# **PBHV9560Z**

600 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor
12 August 2014 **Product data sheet** 

#### 1. **General description**

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8560Z

#### 2. **Features and benefits**

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub>
- High collector current gain hFE at high IC
- AEC-Q101 qualified

### **Applications**

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- HID front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-600	V
I <sub>C</sub>	collector current		_	-	-0.5	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	70	130	-	



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. M
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV9560Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9560Z	HV956Z

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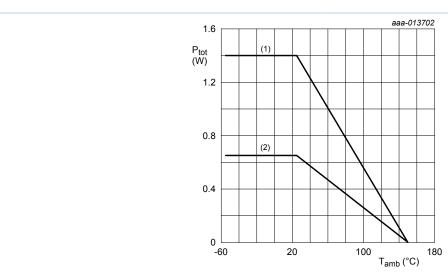
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-600	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-600	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-600	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

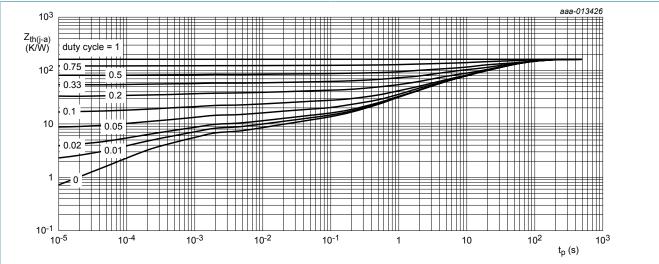
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### Thermal characteristics

Table 6. **Thermal characteristics** 

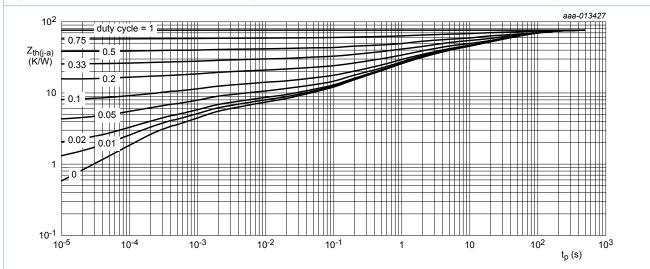
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	190	K/W
			<u>[2]</u>	-	-	89	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, single-sided copper, tin-plated and standard footprint.

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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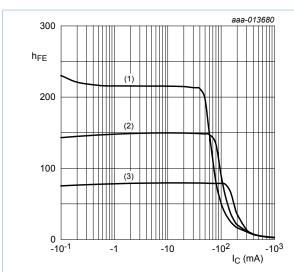
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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -400 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-		-	-100	nA
	current	$V_{CB}$ = -400 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C	-		-	-10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -400 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-		-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-		-	-100	nA
h <sub>FE</sub> DC cu	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	7	<b>'</b> 0	130	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	5	50	90	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -50 mA; $I_B$ = -5 mA; $T_{amb}$ = 25 °C	-		-150	-250	mV
	saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -20 mA; pulsed; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-		-140	-250	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = -50 mA; $I_{B}$ = -5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-		-	-900	mV
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -30 mA; f = 100 MHz	-		38	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-		12	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-		390	-	pF

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$$V_{CE} = -10 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

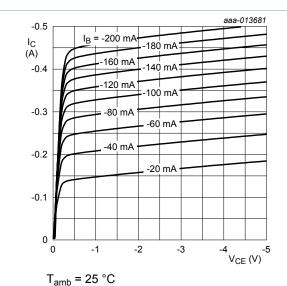
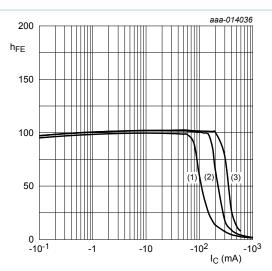


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



$$h_{FE} = f_{(IC)}$$

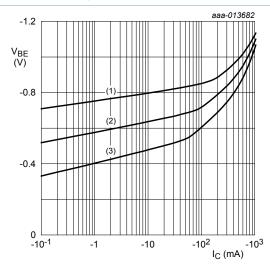
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$V_{CE} = -10 \text{ V}$$

(2) 
$$V_{CE} = -25 \text{ V}$$

(3) 
$$V_{CE} = -50 \text{ V}$$

Fig. 5. DC current gain as a function of collector current; typical values



$$V_{CE} = -5 V$$

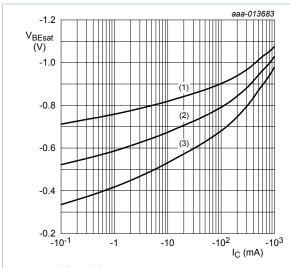
(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values

### 600 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor

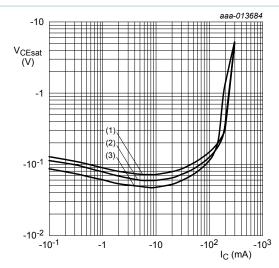


$$I_C/I_B = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C



$$I_C/I_B = 5$$

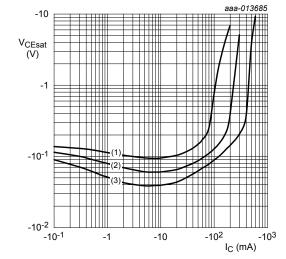
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



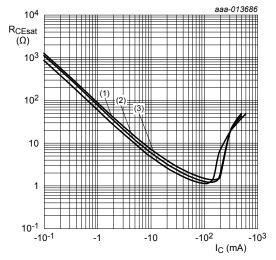
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 10.0$$

(2) 
$$I_C/I_B = 5.0$$

(3) 
$$I_C/I_B = 2.5$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

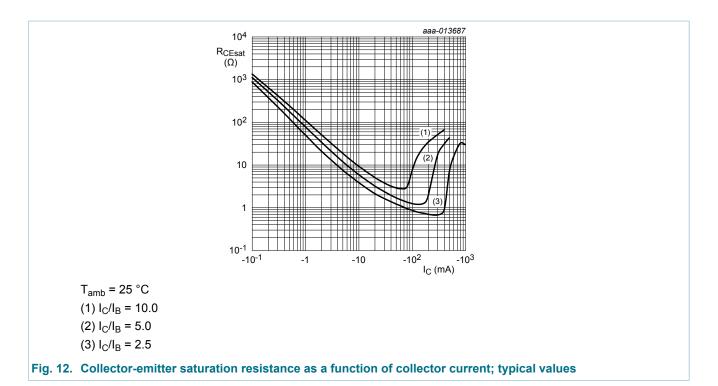
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

### 600 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor



### 11. Test information

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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## 12. Package outline

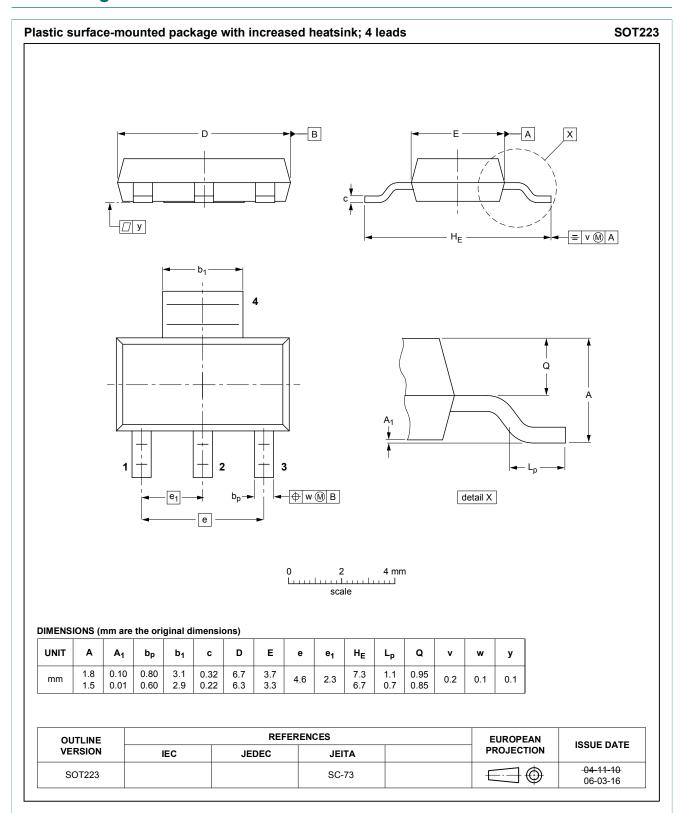
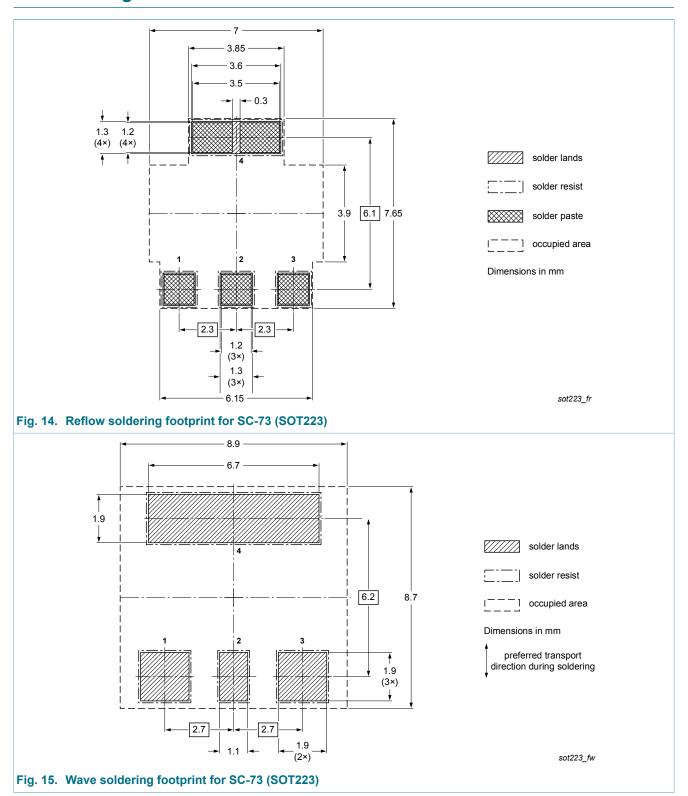


Fig. 13. Package outline SC-73 (SOT223)

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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9560Z v.1	20140812	Product data sheet	-	-

### 600 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor

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